

## **SEMICONDUCTOR MEMORY WITH EMBEDDED DRAM**

### **ABSTRACT**

A semiconductor memory comprises a plurality of memory cells, for example  
5 Flash memory cells, arranged in a plurality of lines, and a plurality of memory cell  
access signal lines, each one associated with at least one respective line of  
memory cells, for accessing the memory cells of the at least one respective line of  
memory cells; each signal line has a capacitance intrinsically associated therewith.  
A plurality of volatile memory cells is provided, each having a capacitive storage  
10 element. Each volatile memory cell is associated with a respective signal line, and  
the respective capacitive storage element formed by the capacitance intrinsically  
associated with the respective signal lines. In particular, the parasitic capacitances  
associated with bit lines of a matrix of memory cells can be exploited as capacitive  
storage elements.

15